

WR0459I 矽 NPN 三极管 1 封装 Silicon NPN transistor in a TO-18 Plastic Package.

高 V_{CE0} 耐压
High V_{CE0}

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	100	mA
Collector Current – Continuous(Pulse)	I_{CP}	200	mA
Collector Power Dissipation	P_C	1.2	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

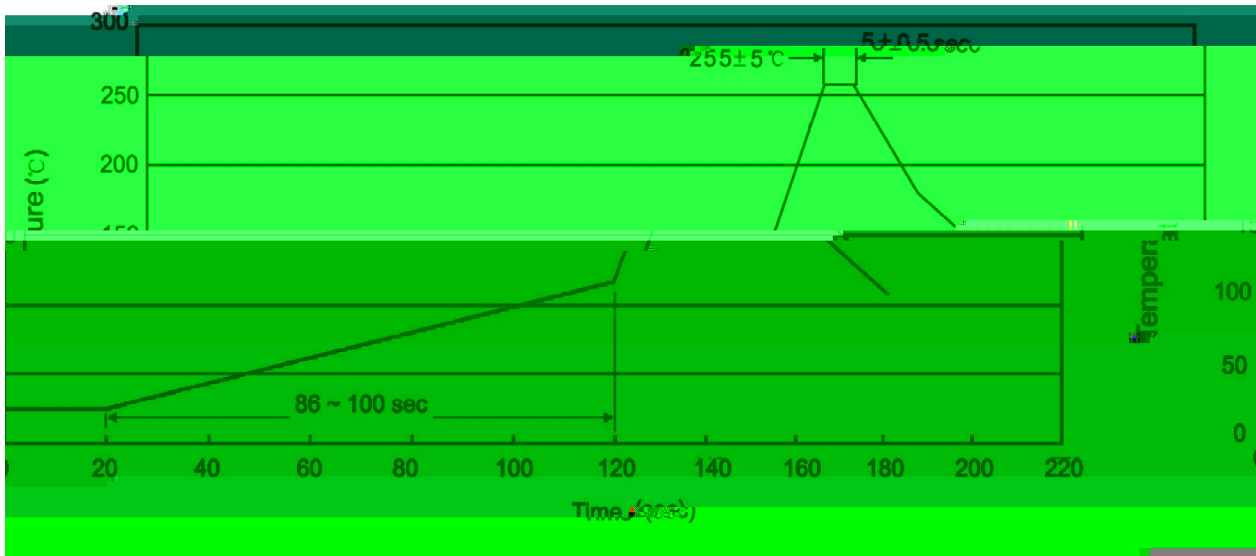
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=10\mu A$ $I_E=0$	300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=0.1mA$ $I_B=0$	300			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10\mu A$ $I_C=0$	7.0			V
DC Current Gain	h_{FE}	$V_{CE}=50V$ $I_C=5.0mA$	50		250	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=30mA$ $I_B=3.0mA$			1.5	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=10V$ $I_C=30mA$			1.2	V
Transition Frequency	f_T	$V_{CB}=30V$ $I_C=20mA$	70	140		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=30V$ $I_E=0$ $f=1.0MHz$		2.4		pF

/ Package Dimensions



Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. Прогрев: 25~150 °C, Time: 60~90sec;

2. Температура: 255±5 °C, Time: 5±0.5sec;

3. Скорость охлаждения: 2~10 °C/sec

Note:

1.Preheating:25~150 °C , Time:60~90sec.

2.Peak Temp.:255±5 °C , Duration:5±0.5sec.

3. Cooling Speed: 2~10 °C/sec.

P8358SPEC. (Cooling